

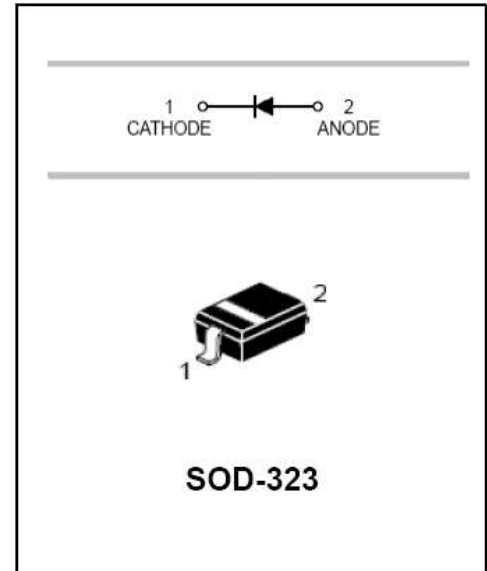
Schottky Barrier Diode

FEATURES

- Low Forward Voltage Drop.
- Guard Ring Construction For Transient Protection.
- Negligible Reverse Recovery Time.
- Low Reverse Capacitance.

APPLICATIONS

- Schottky barrier switching.



MAXIMUM RATING @ Ta=25°C unless otherwise specified

Parameter	Symbol		Unit
Peak Repetitive Peak reverse voltage	V_{RR}		
Working Peak DC Reverse Voltage	V_{RWM}	30	V
	V_R		
RMS Reverse Voltage	$V_{R(RMS)}$	28	V
Forward Continuous Current	I_F	150	mA
Repetitive Peak Forward Current @t≤1.0s	I_{FRM}	1.5	A
Power Dissipation	P_d	400	mW
Thermal Resistance Junction to Ambient	$R_{\theta jA}$	300	°C/W
Storage temperature	T_{stg}	-65~+125	°C

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	$V_{(BR)R}$	30			V	$I_R=10\mu A$
Forward voltage	V_F			0.4 0.8	V	$I_F=20mA$ $I_F=200mA$
Reverse current	I_{RM}			5.0	μA	$V_R=30V$ $V_R=20V$ $V_R=10V$
Capacitance between terminals	C_T		50		pF	$V_R=0, f=1MHz$
Reverse Recovery Time	t_{rr}		10		ns	$I_R=I_F=200mA$ $I_{rr}=0.1*I_R, R_L=100\Omega$

TYPICAL CHARACTERISTICS

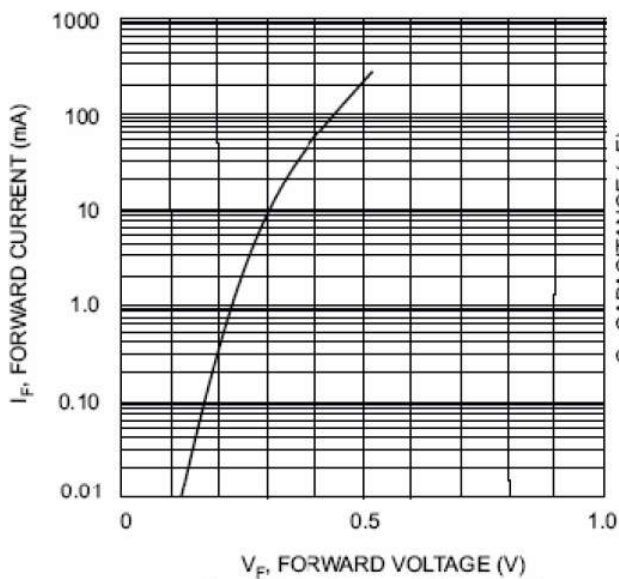


Fig. 1 Typical Forward Characteristics

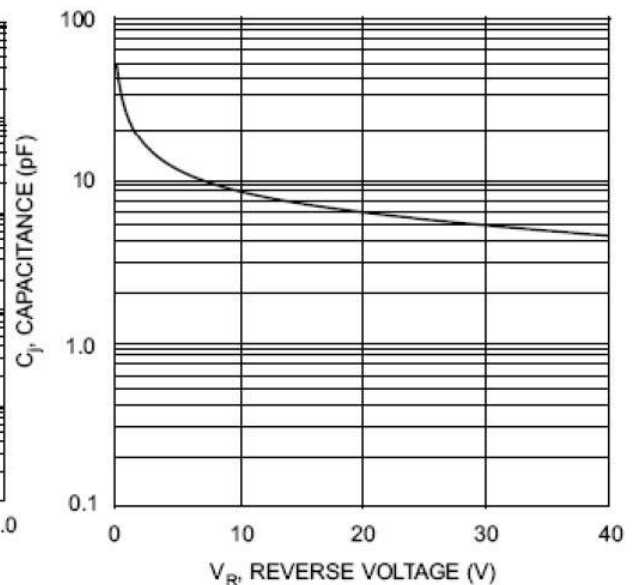


Fig. 2 Typ. Junction Capacitance vs Reverse Voltage

单击下面可查看定价，库存，交付和生命周期等信息

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